ABSTRACT OF THE DISCLOSURE

The method of the present invention is a method of forming a pattern by using a photomask having both a minute aperture where the main component of a transmitted light is an evanescent light and an aperture where the main component of a transmitted light is a propagating light, comprising the steps of forming a photoresist with a film thickness equal to or smaller than a width of the minute aperture on a substrate to be processed, and exposing the photoresist by an incident light for exposure. The apparatus of the present invention is an apparatus for forming a pattern by using a photomask having both a minute aperture where the main component of a transmitted light is an evanescent light and an aperture where the main component of a transmitted light is a propagating light, comprising a sample stand for placing a substrate to be processed on which a photoresist with a film thickness equal to or smaller than a width of the minute aperture is formed, a stage for placing the photomask, a light source for generating light for exposure, and an unit for controlling a distance between the substrate to be processed and the photomask.